MOTOR® MA供应商 SEMICONDUCTOR TECHNICAL DATA

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by MRF1090MA/D

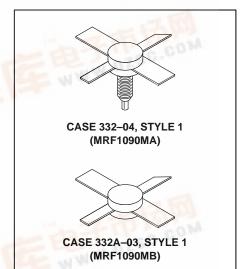
The RF Line Microwave Pulse Power Transistors

Designed for Class B and C common base amplifier applications in short pulse TACAN, IFF, and DME transmitters.

- Guaranteed Performance @ 1090 MHz, 50 Vdc Output Power = 90 Watts Peak Minimum Gain = 8.4 dB
- 100% Tested for Load Mismatch at All Phase Angles with 10:1 VSWR
- Industry Standard Package
- Nitride Passivated
- Gold Metallized for Long Life and Resistance to Metal Migration
- Internal Input Matching for Broadband Operation
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.



90 W PEAK, 960–1215 MHz MICROWAVE POWER TRANSISTORS NPN SILICON



MAXIMUM RATINGS

	and the second se		
Rating	Symbol	Value	Unit
Collector-Base Voltage	VCBO	70	Vdc
Emitter-Base Voltage	VEBO	4.0	Vdc
Collector–Current — Peak (1)	IC	6.0	Adc
Total Device Dissipation @ T _C = 25°C (1) (2) Derate above 25°C	PD	290 1.66	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic		Мах	Unit
Thermal Resistance, Junction to Case (3)	R _{θJC}	0.6	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•			-510	Cert .
Collector–Emitter Breakdown Voltage ($I_C = 25 \text{ mAdc}, V_{BE} = 0$)	V _(BR) CES	70	ET.	DZSC.	Vdc
Collector–Base Breakdown Voltage (I _C = 25 mAdc, I _E = 0)	V(BR)CBO	70	AT AL	-	Vdc
Emitter–Base Breakdown Voltage (I _E = 5.0 mAdc, I _C = 0)	V _{(BR)E} BO	4.0	—	-	Vdc
Collector Cutoff Current $(V_{CB} = 50 \text{ Vdc}, I_E = 0)$	ІСВО	—	_	5.0	mAdc
ON CHARACTERISTICS	•		•	•	•
DC Current Gain (4)	hee	10	30	_	_

	''FE	
(I _C = 2.5 Adc, V _{CE} = 5.0 Vdc)		

NOTES:

frevsc.com

1. Pulse Width = 10 μ s, Duty Cycle = 1%.

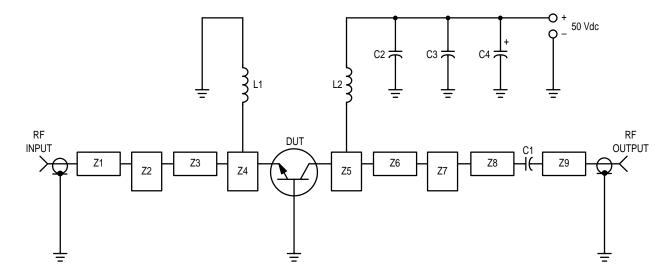
These devices are designed for RF operation. The total device dissipation rating applies only when the device is operated as RF amplifiers.
Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.
80 µs Pulse on Tektronix 576 or equivalent.



(continued)

Characteristic	Symbol	Min	Тур	Max	Unit		
DYNAMIC CHARACTERISTICS							
Output Capacitance ($V_{CB} = 50 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)	C _{ob}	-	12	16	pF		
FUNCTIONAL TESTS (Pulse Width = 10 µs, Duty Cycle = 1.0%)	-	-				
Common–Base Amplifier Power Gain (V _{CC} = 50 Vdc, P _{out} = 90 W pk, f = 1090 MHz)	GPB	8.4	10.8	_	dB		
Collector Efficiency (V _{CC} = 50 Vdc, P _{out} = 90 W pk, f = 1090 MHz)	η	35	40	_	%		
Load Mismatch (V _{CC} = 50 Vdc, P _{out} = 90 W pk, f = 1090 MHz, VSWR = 10:1 All Phase Angles)	Ψ	No Degradation in Power Output					

ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^{\circ}C$ unless otherwise noted)



C1, C2 — 220 pF Chip Capacitor, 100–mil ATC C3 — 0.1 μ F C4 — 47 μ F/75 V L1, L2 — 3 Turns #18 AWG, 1/8″ ID Z1–Z9 — Distributed Microstrip Elements,

See Photomaster

Board Material — 0.031" Thick Glass Teflon, ϵ_{f} = 2.5



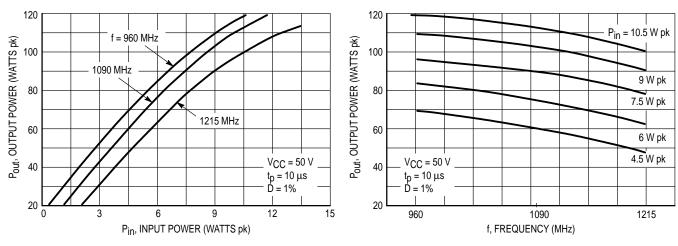




Figure 3. Output Power versus Frequency

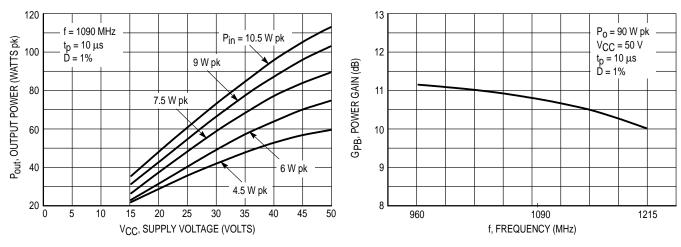
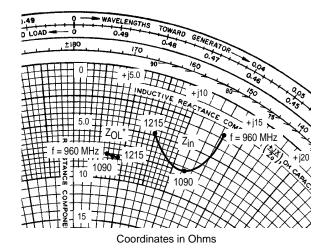


Figure 4. Output Power versus Supply Voltage

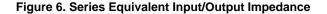
Figure 5. Power Gain versus Frequency



	= 90 W pk p = 10 μs	
f	Z _{in}	Z _{OL} *

f	Z _{in}	Z _{OL} *
MHz	Ohms	Ohms
960	2.8 + j13.2	7.6 + j3.5
1090	7.4 + j11.4	7.6 + j4.0
1215	4.7 + j7.5	7.7 + j4.5

Z_{OL}* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage, and frequency.



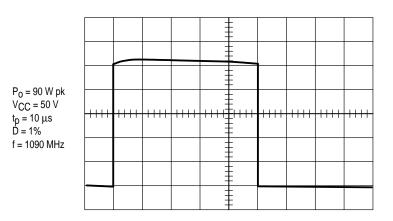
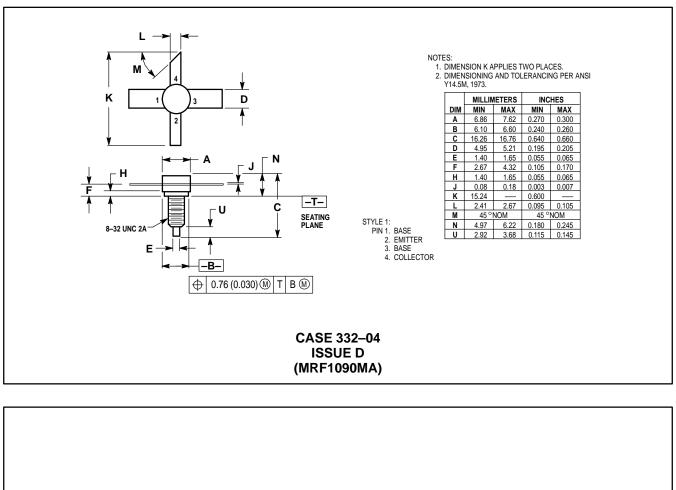
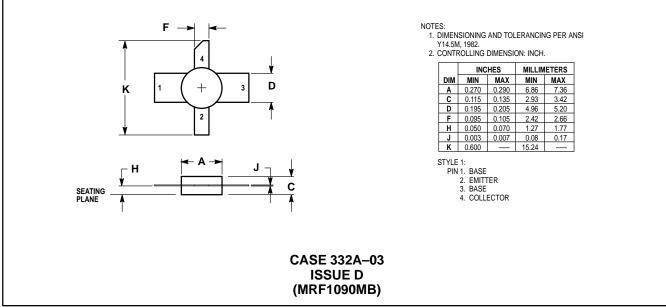


Figure 7. Typical Pulse Performance

PACKAGE DIMENSIONS





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